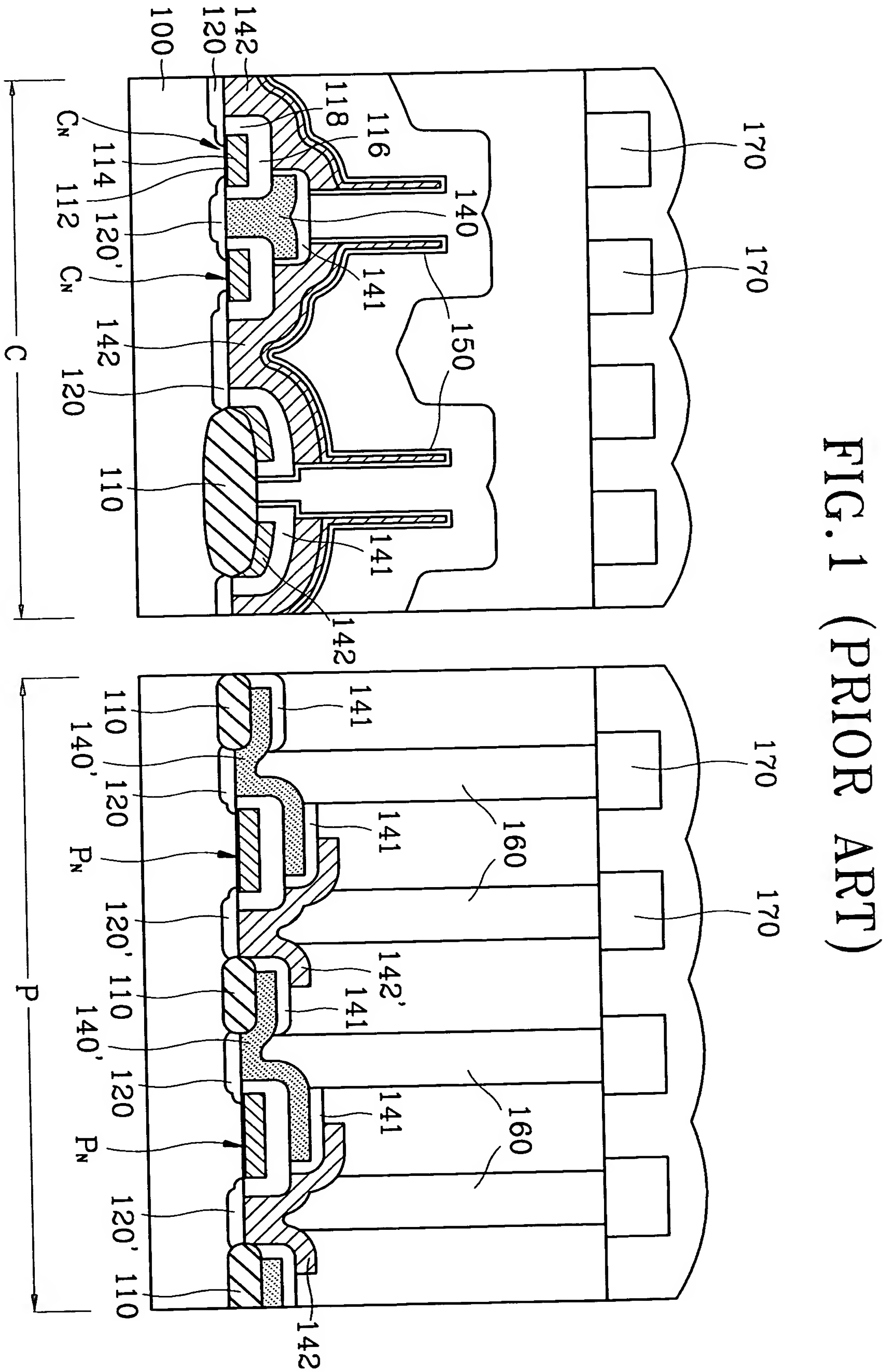


FIG. 1 (PRIOR ART)

FIG. 2

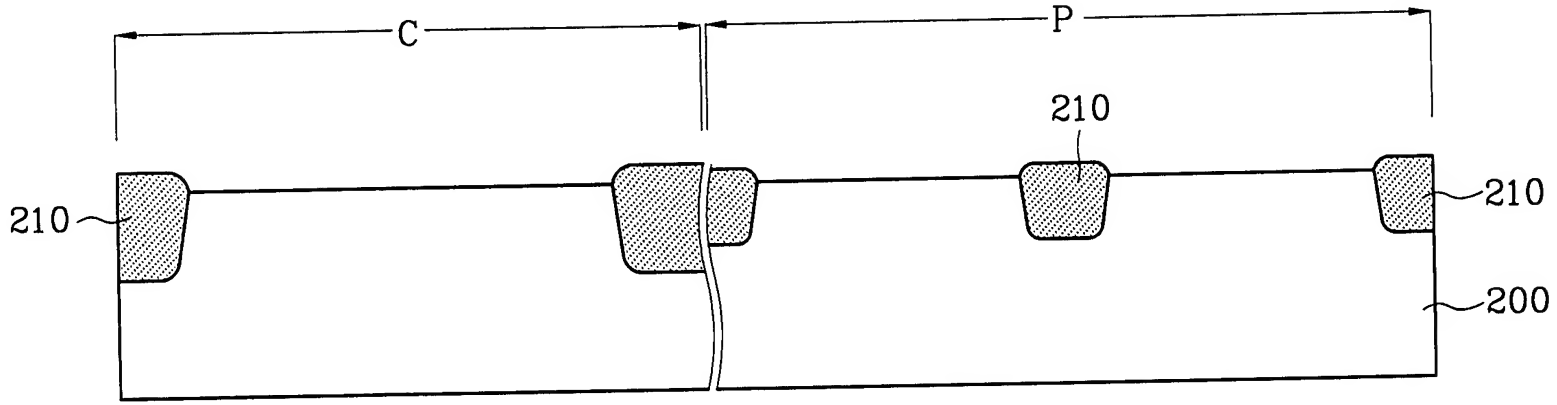
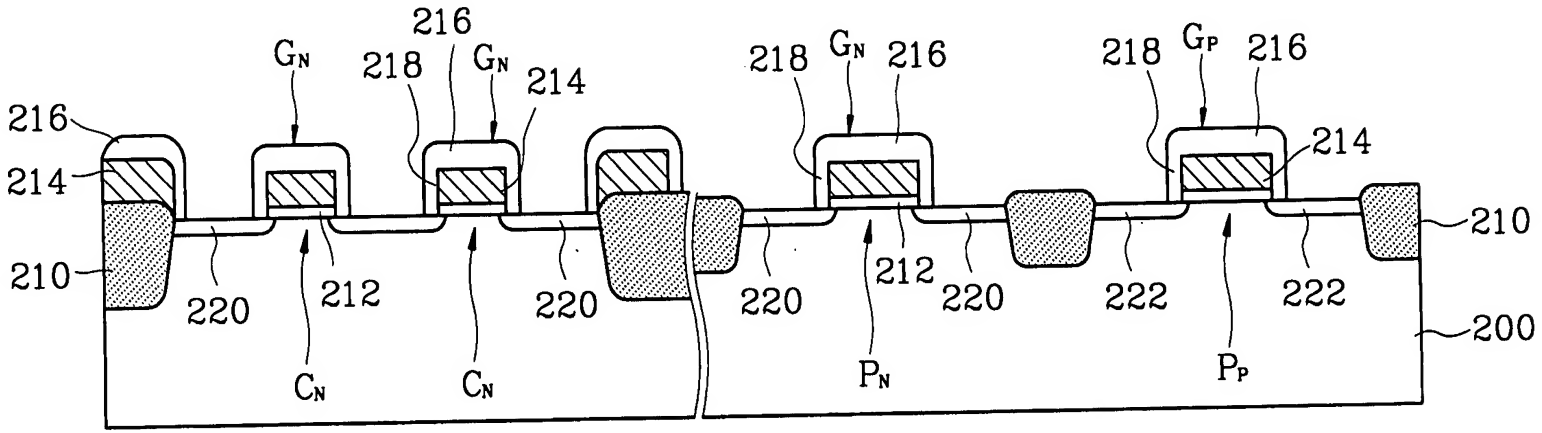


FIG. 3



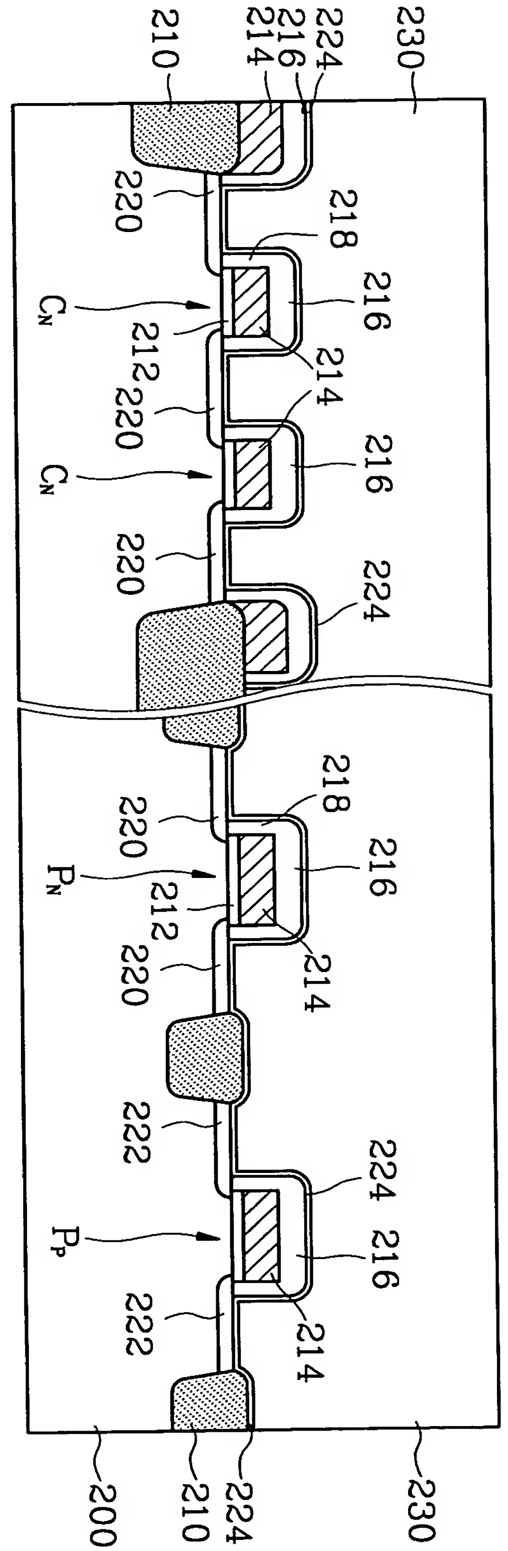


FIG. 4

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FIG. 5

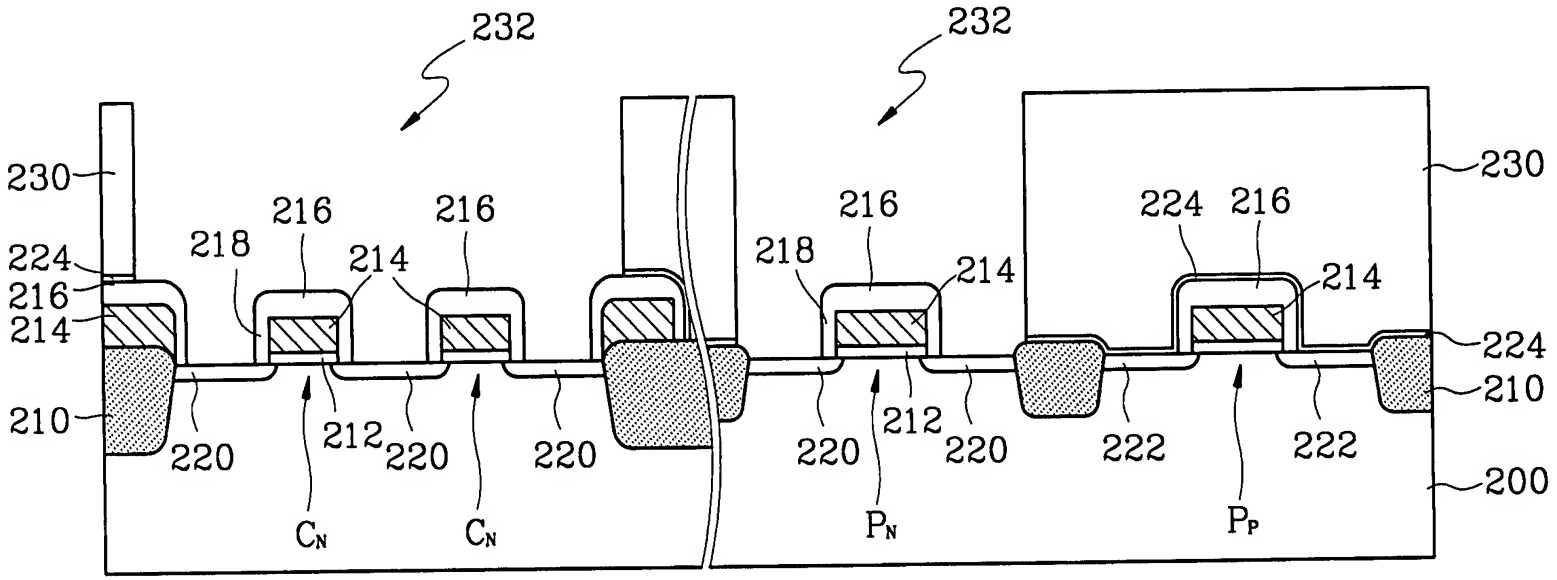
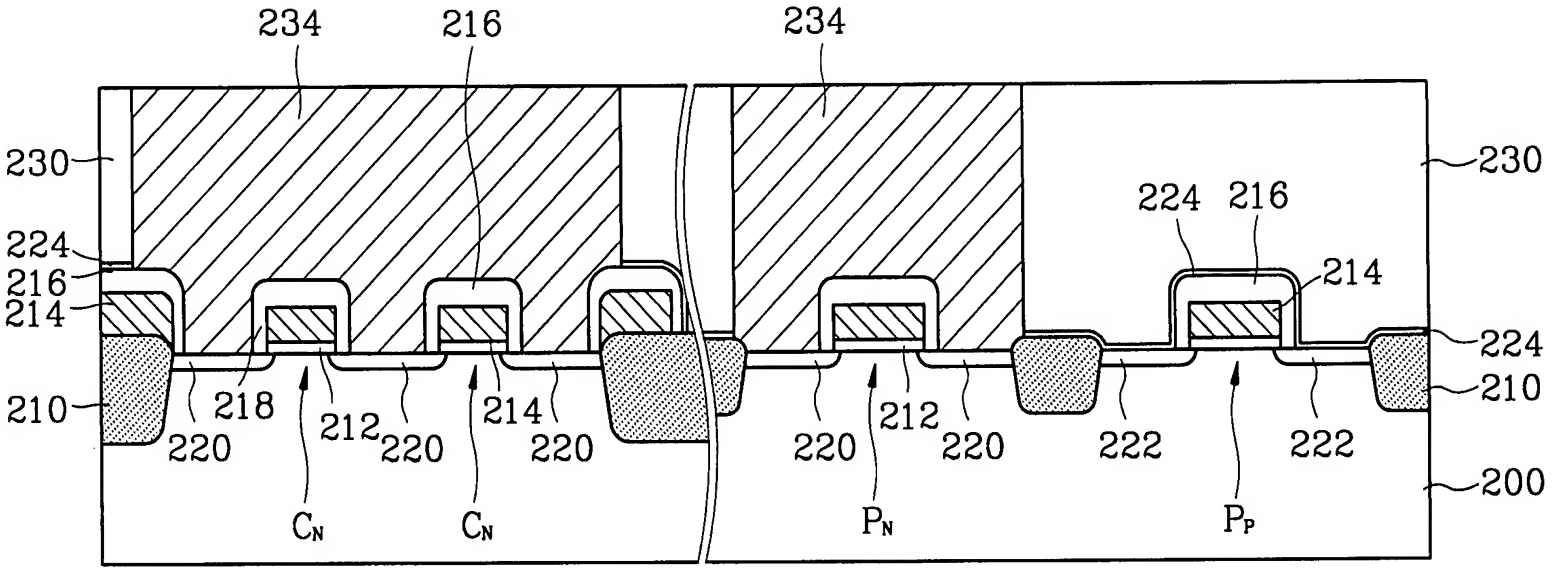


FIG. 6



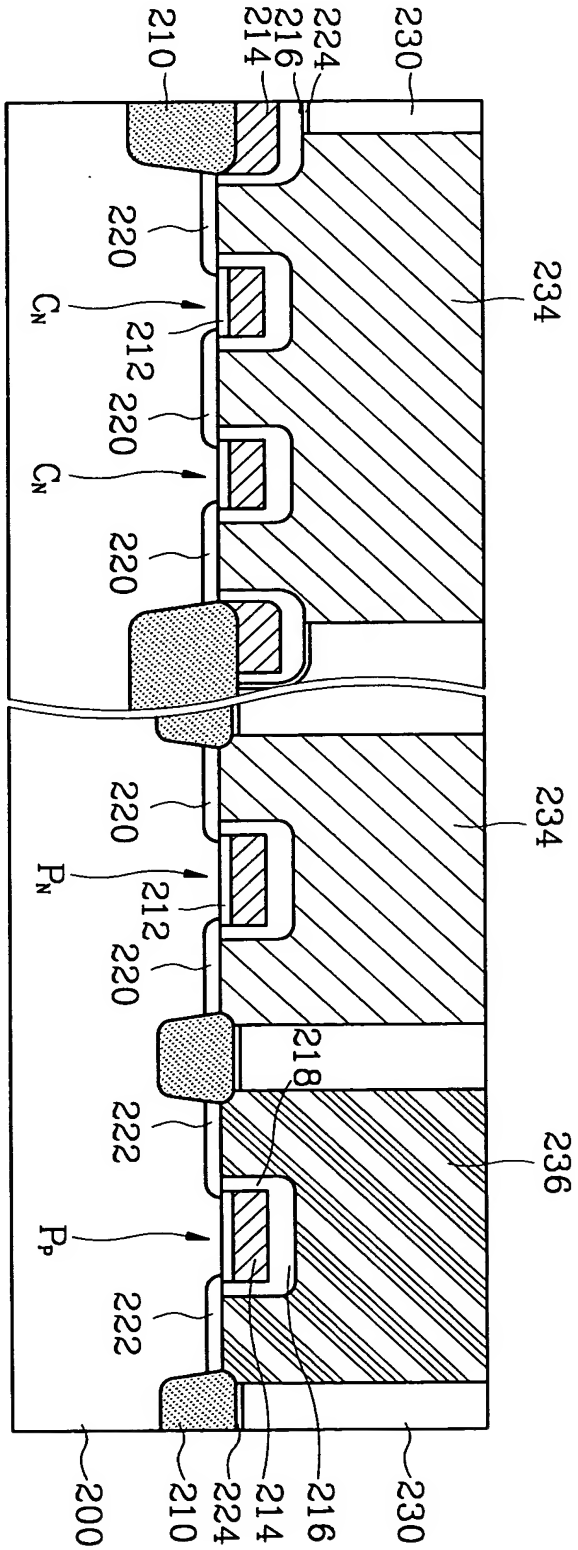


FIG. 7

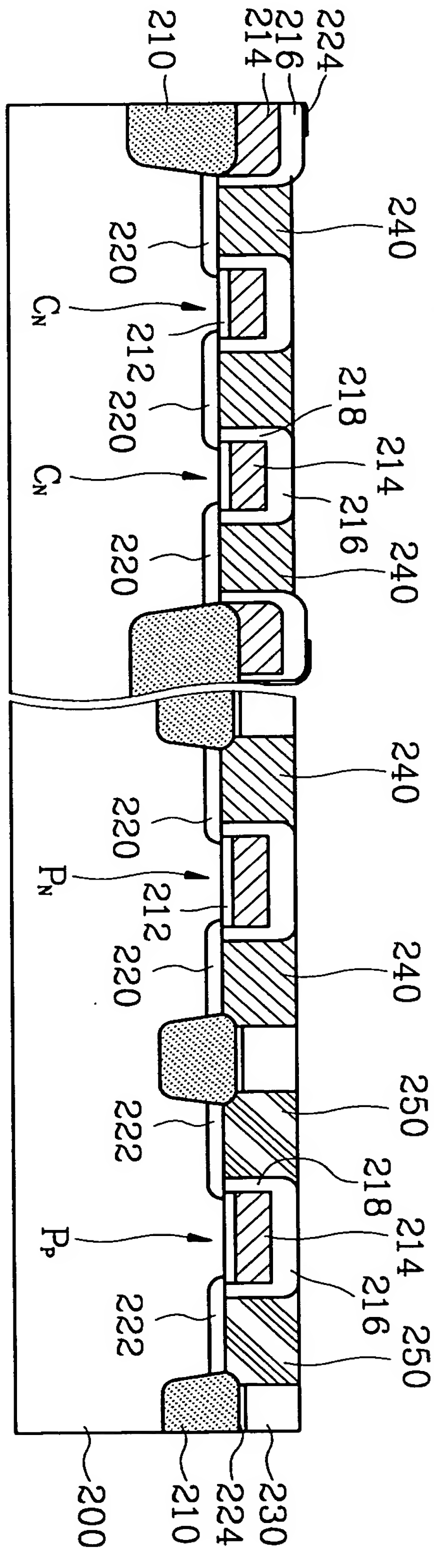


FIG. 8

FIG. 9

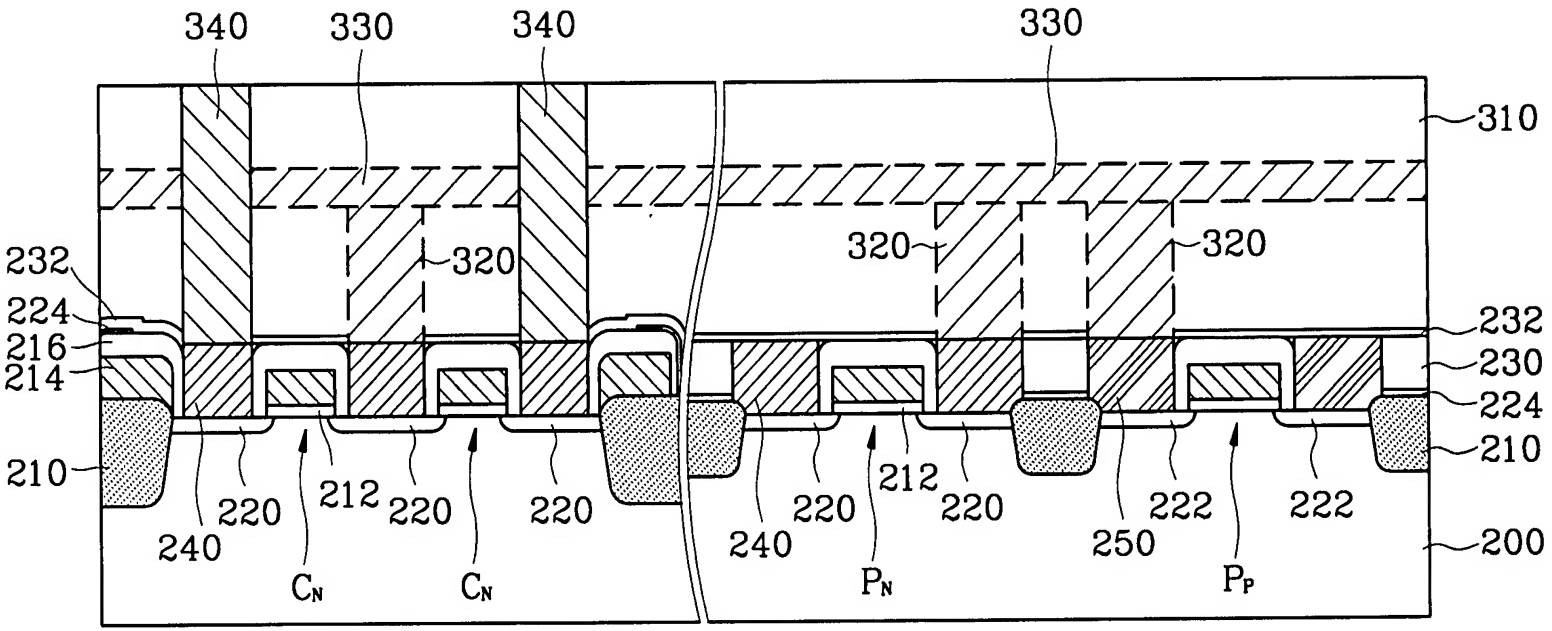


FIG. 10

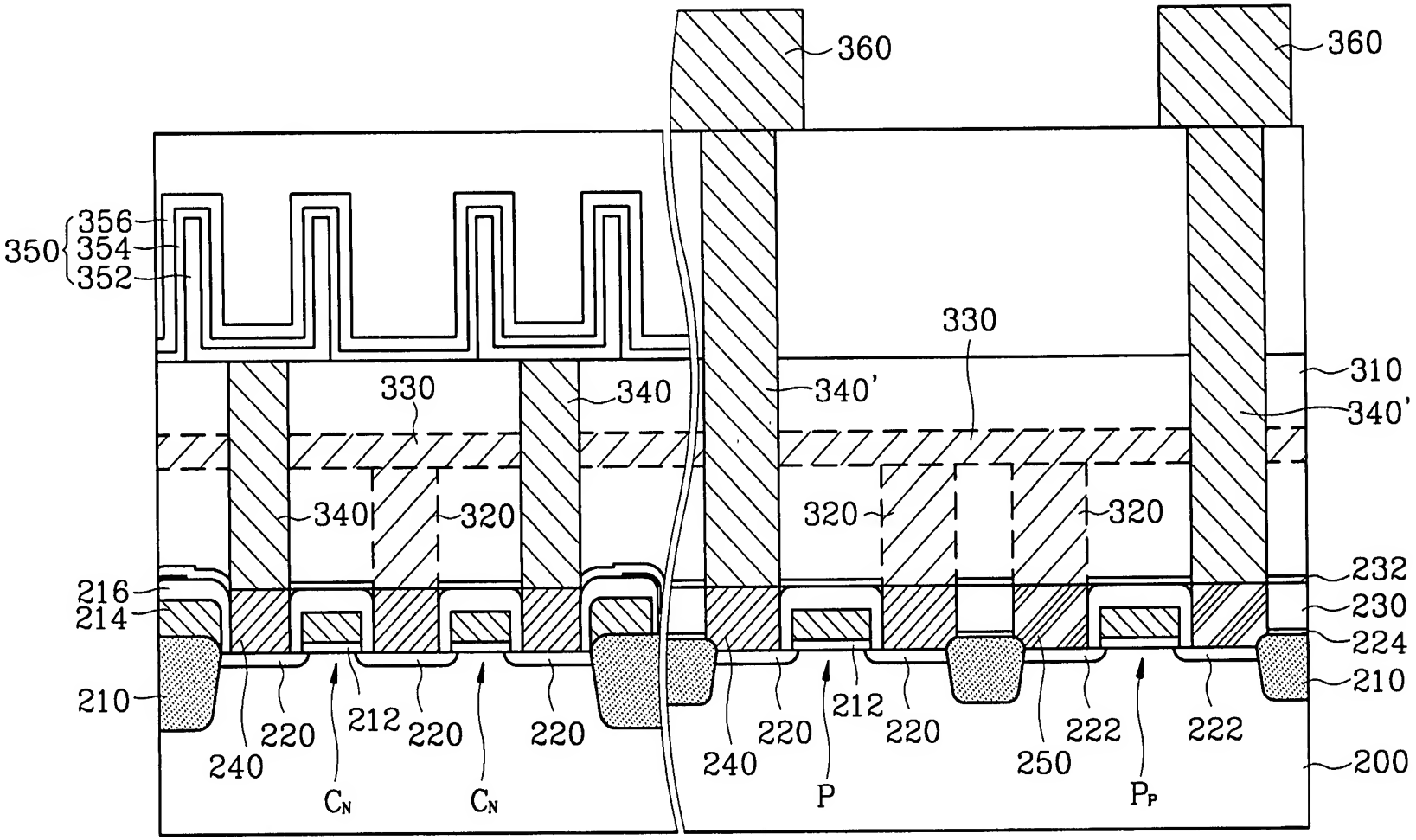


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FIG. 11

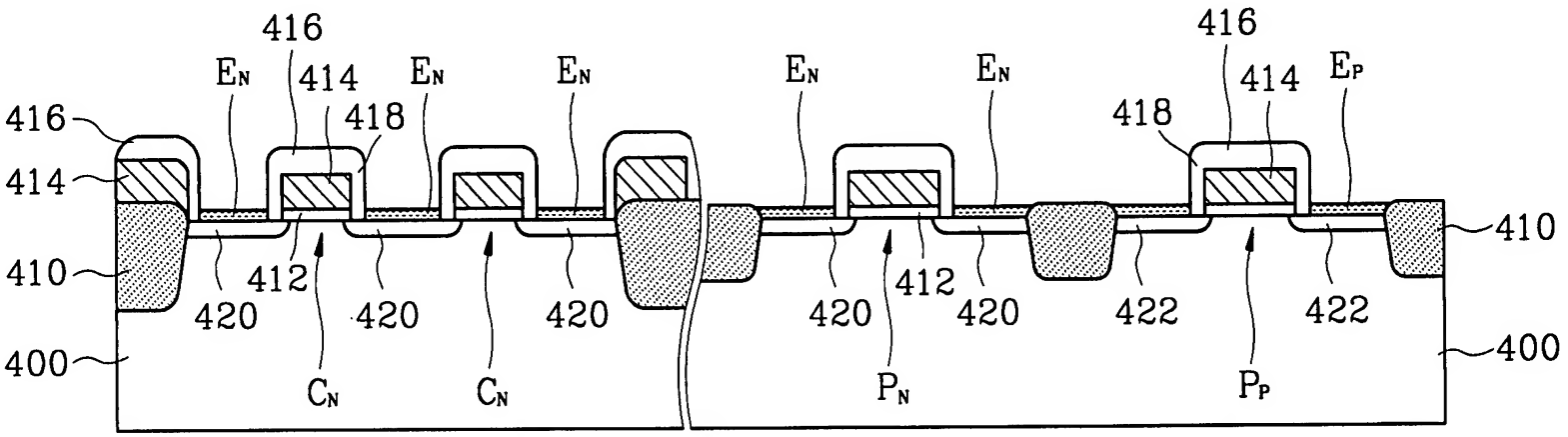

FIG. 12

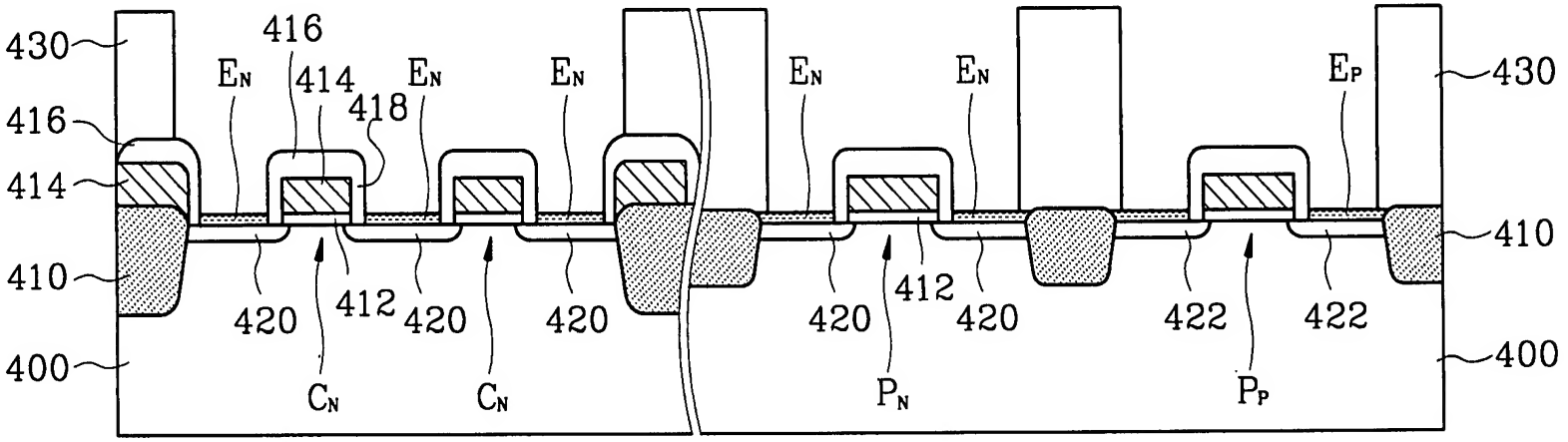

FIG. 13

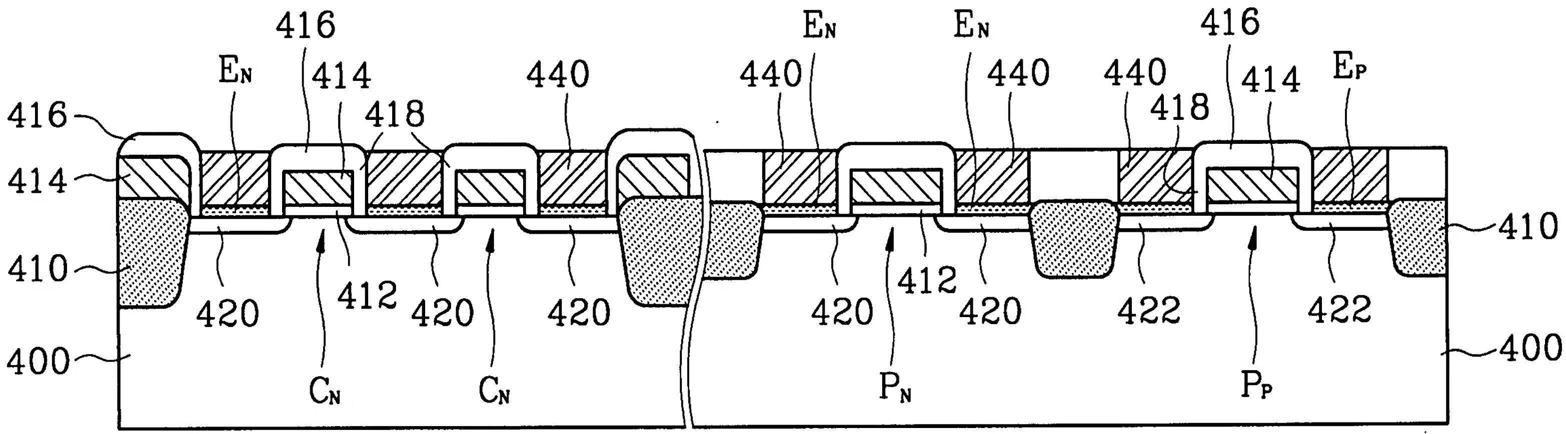

FIG. 14A

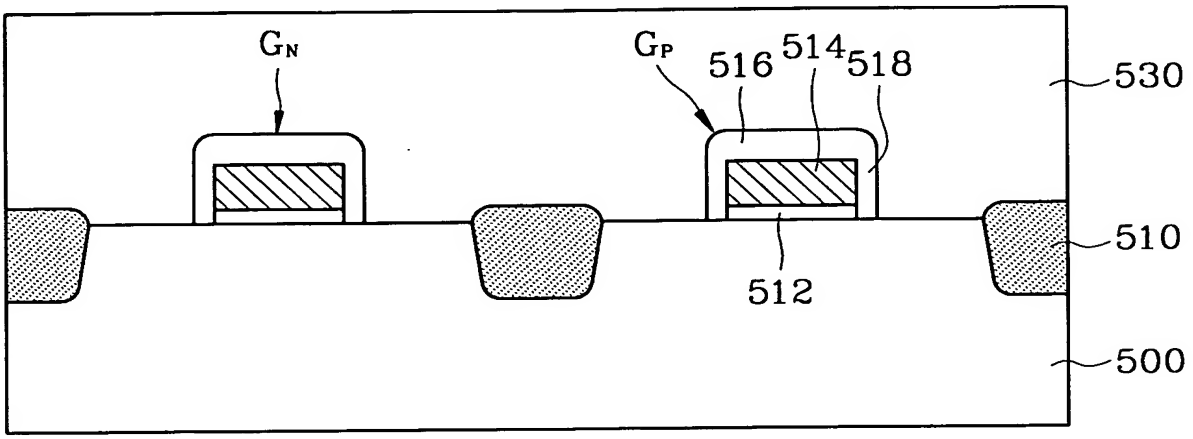

FIG. 14B

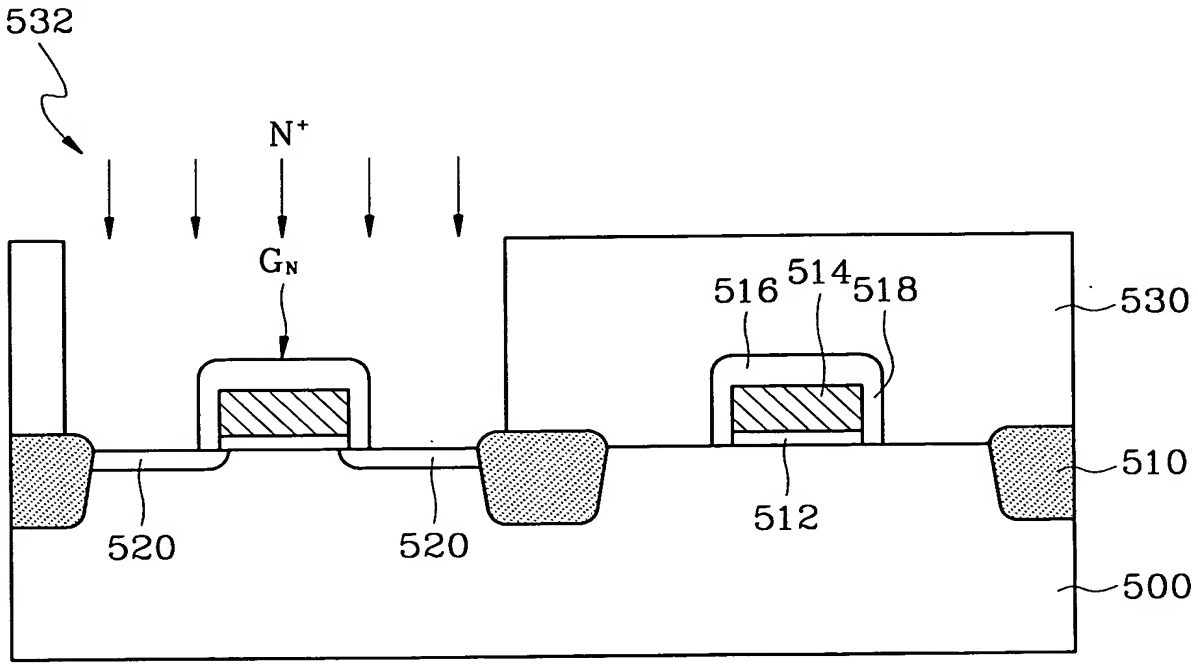

FIG. 14C

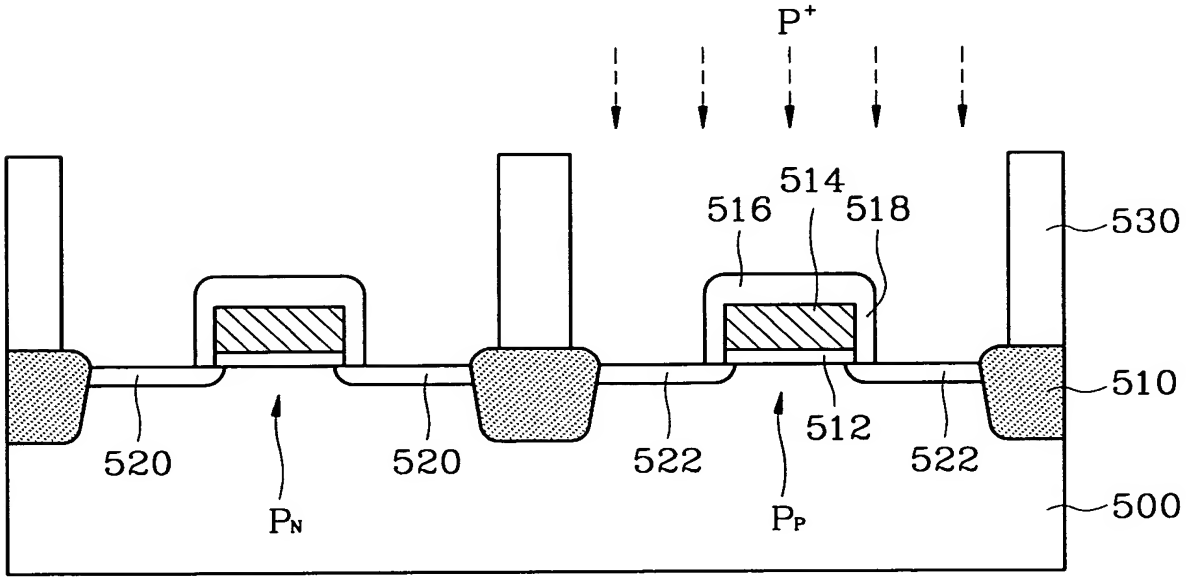

FIG. 14D

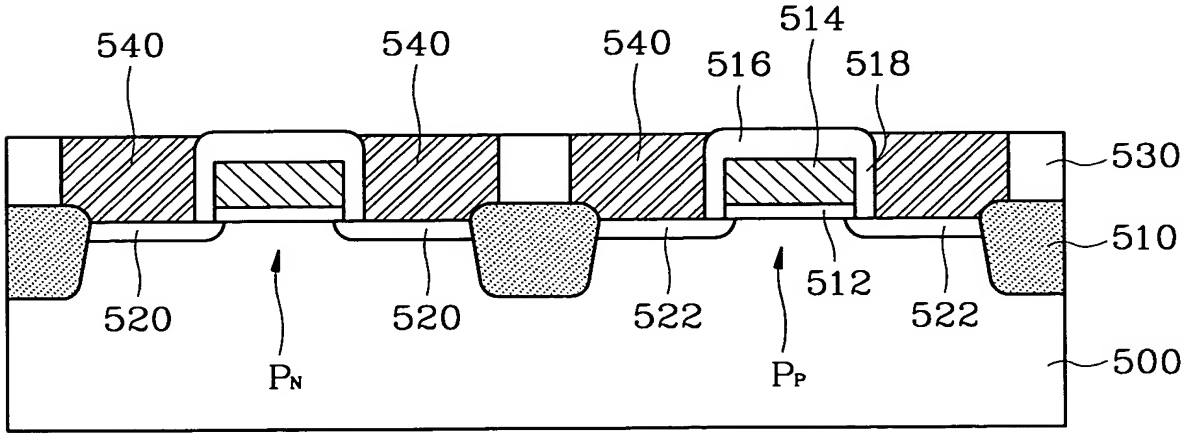

FIG. 15A

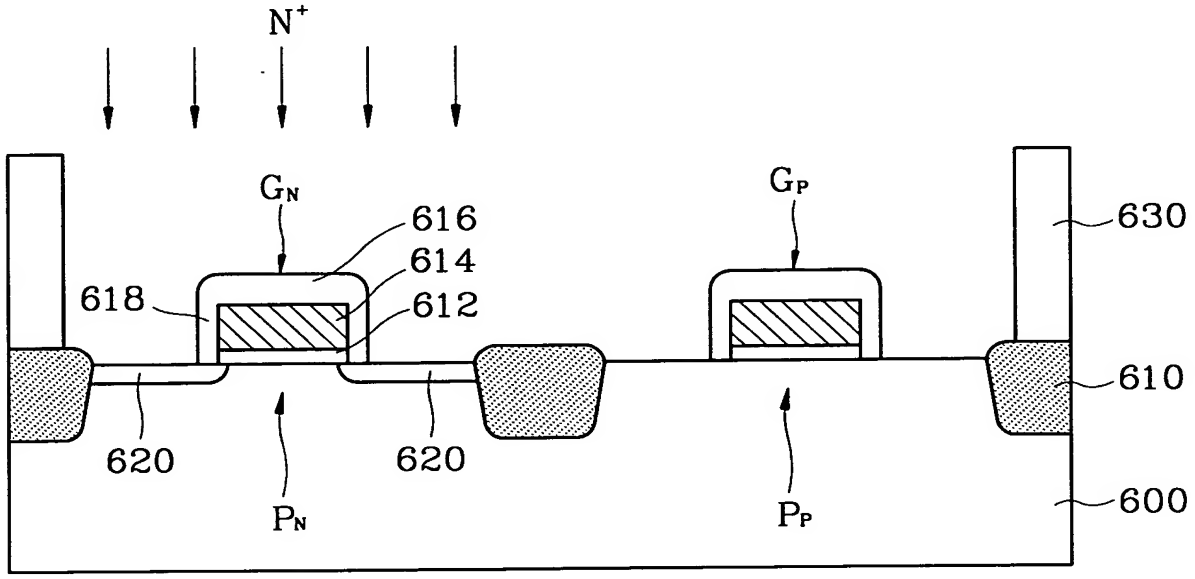

FIG. 15B

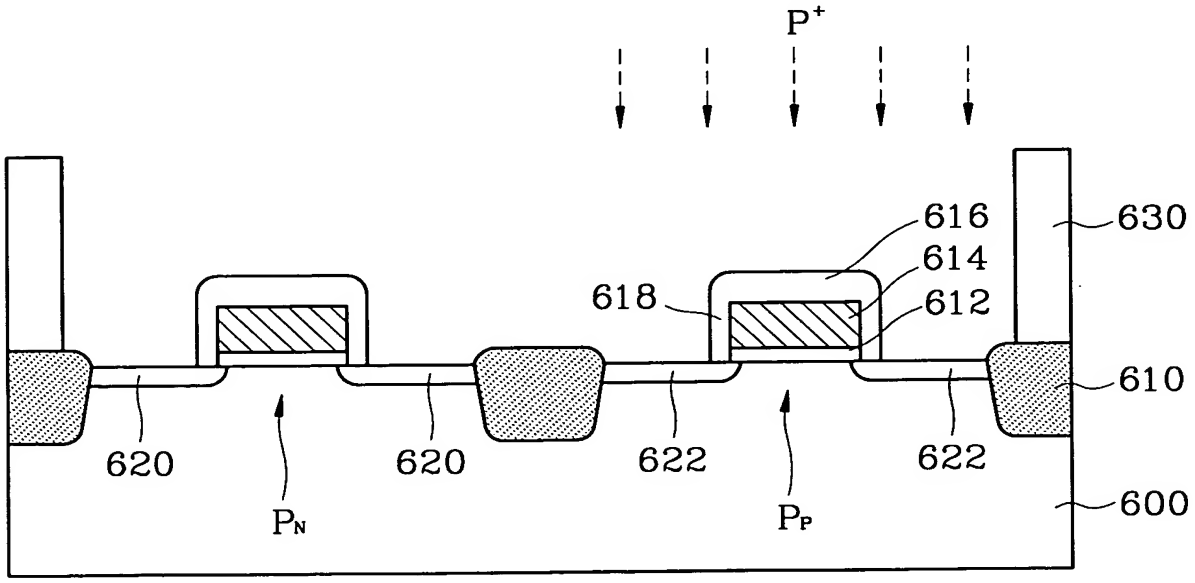

FIG. 15C

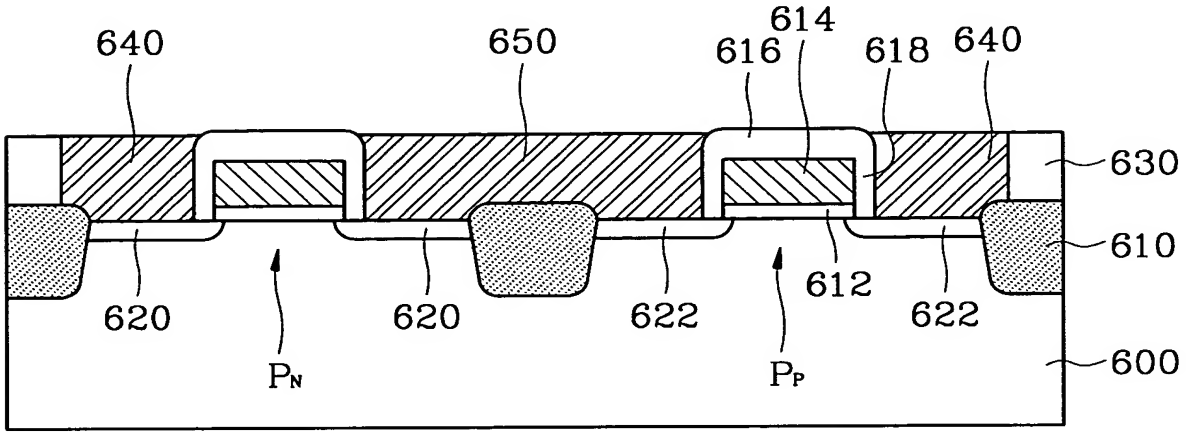

FIG. 16 (PRIOR ART)